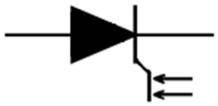
高端电力电子器件和装置制造商

TL353-630-7200

光 控 晶 闸 管

- V_{DRM} = **7200 V**
- V_{RRM} = **7200 V**
- $I_{T(AV)}$ = **670 A** (T_C = 70°C)
- $I_{T(AV)}$ = **540 A** (T_C = 85°C)
- I_{TSM} = **10.5 kA** (T_j = 120°C)
- P_{LM} = **40 mW**



- Light triggering
- Low on-state and switching losses

MAXIMUM RATED VALUES

Parameter and conditions	Symbol	Values	Units
Repetitive peak off-state voltage, T_j = -40 …+ 120°C	V_{DRM}	7200	V
Repetitive peak reverse voltage, T_j = -40 …+ 120°C	V_{RRM}	7200	
Non-repetitive peak off-state voltage, T_j = -40 …+ 120°C	V_{DSM}	7300	
Non- repetitive peak reverse voltage, T_j = -40 …+ 120°C	V_{RSM}	7300	
Repetitive peak off-state current/ Repetitive peak reverse current, T_j = 120°C, V_D / V_R = V_{DRM} / V_{RRM}	I_{DRM} / I_{RRM}	150	mA
Average on-state current, f = 50 Hz, double side cooling T_C = 85°C T_C = 70°C	$I_{T(AV)}$	 540 670	A
RMS on-state current, T_C = 70°C, f = 50 Hz	I_{TRMS}	1060	
Surge non-repetitive on-state current, T_j = 120°C, V_R = 0, t_p = 10 ms	I_{TSM}	10.5	kA
Safety factor	I^2t	5.5×10^5	A^2s
Critical rate of rise of on-state current, T_j = 120°C, V_D = 0.67V_{DRM}, I_T = 1260 A, P_{LM} = 40 mW, t_L = 10 µs, f = 50 Hz	$(di_T/dt)_{crit}$	300	A/µs
Critical rate of rise of off-state voltage, T_j = 120°C, V_D = 0.67V_{DRM}	$(dv_D/dt)_{crit}$	1000 - 2000	V/µs
Minimum gate trigger light power, T_j = 25°C, V_D = 12 V	P_{LM}	40	mW
Operation junction temperature range	T_j	-40 … +120	°C
Storage temperature range	T_{stg}	-40 … +50	

北京新创椿树整流器件有限公司

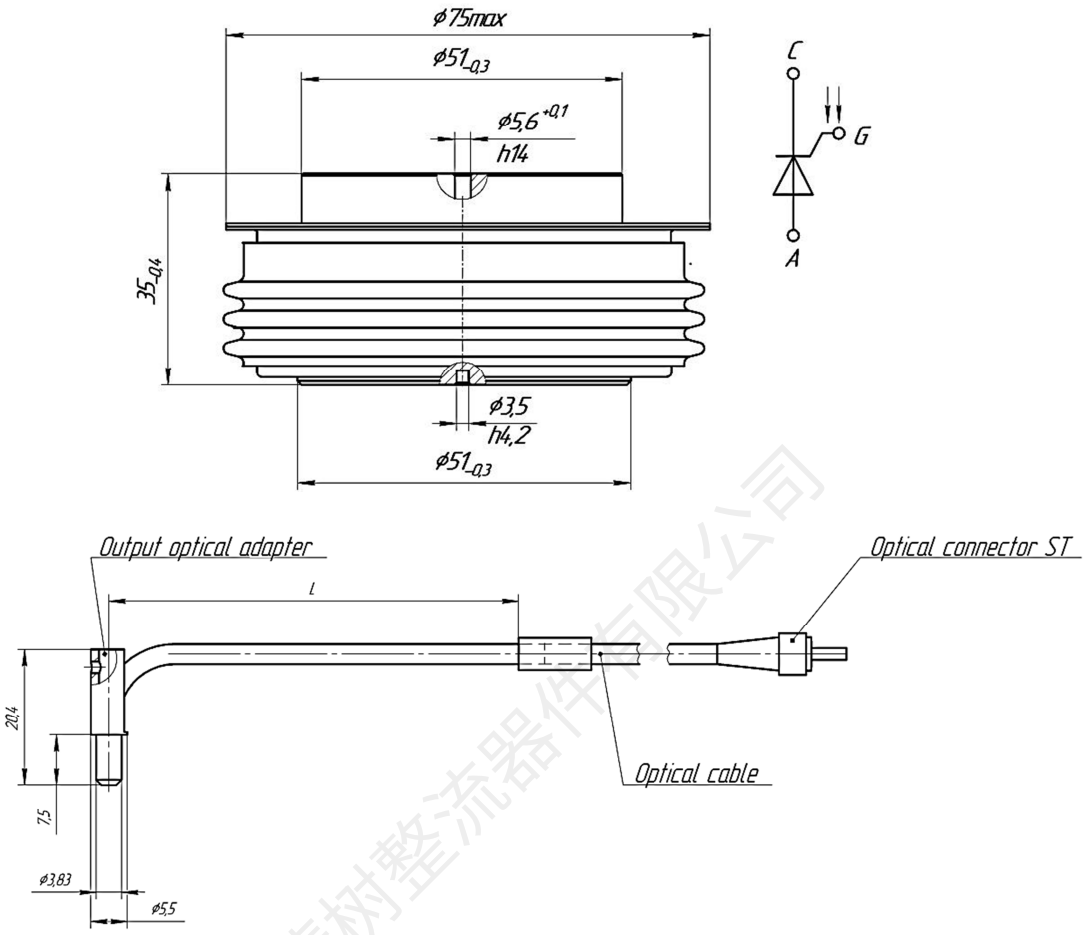
 © 2020 Chunzheng all rights reserved

ELECTRICAL CHARACTERISTICS

Parameter and conditions	Symbol	Values			Units
		min	typ.	max	
Peak on-state voltage, T_j = 25°C, I_T = 1980 A	V_{TM}	-	-	3.00	V
On-state threshold voltage, T_j = 120°C, I_T = 1000 - 3000 A	$V_{T(TO)}$	-	-	1.26	
On-state slope resistance, T_j = 120°C, I_T = 1000 - 3000 A	r_T	-	-	1.47	mΩ
Delay time, T_j = 25°C, V_D = 1000 V, I_T = 630 A, P_{LM} = 40 mW, t_L = 10 µs, t_r = 0.5 µs	t_d	-	-	5.0	µs
Turn off-time, T_j = 120°C, I_T = 630 A, di_T/dt = -5 A/µs, V_R ≥ 100 V, V_D = 0.67V_{DRM}, dv_D/dt = 50 V/µs	t_q	-	900	-	
Reverse recovery charge, T_j = 120 °C, I_T = 630 A, di_T/dt = -5 A/µs, V_R ≥ 100 V	Q_{RR}	-	-	3000	µAs
Holding current, T_j = 25°C, V_D = 12 V	I_H	-	-	100	mA
Latching current, T_j = 25°C, V_D = 12 V, P_{LM} = 40 mW, t_L = 10 µs, t_r = 0.5 µs	I_L	-	-	1000	
THERMAL PARAMETERS					
Thermal junction to case resistance, sin 180°: double side cooled DC: double side cooled	 $R_{th(j-c)}$ $R_{th(j-c)}$	-	-	 0.0200 0.0190	°C/W
Thermal resistance case to heatsink, double side cooled single side cooled	$R_{th(c-h)}$	-	-	 0.005 0.010	
MECHANICAL PARAMETERS					
Weight	w	-	0.65	-	kg
Clamping force	F	20	-	26	kN
Maximum acceleration (at nominal mounting force)	a	-	-	50	m/s^2
Minimal cathode-anode distance on insulator surface	D_s	-	28.8	-	mm
Air strike distance	D_a	-	22.5	-	

北京纯博树整流器件有限公司

 © 2020 Chunzheng all rights reserved



Designation	L,mm
Optical adapter OA57	57
Optical adapter OA65	65

C – Cathode, A – Anode, G –Gate

Device Outline Drawing

(dimensions in mm)

Recommended optical interface cable – OA57.

北京纯川椿树整流器件有限公司

 © 2020 Chunzheng all rights reserved